

Features

- Advanced SGT MOS Technology
- Low $R_{DS(ON)}$
- 100% EAS Guaranteed
- Green Device Available

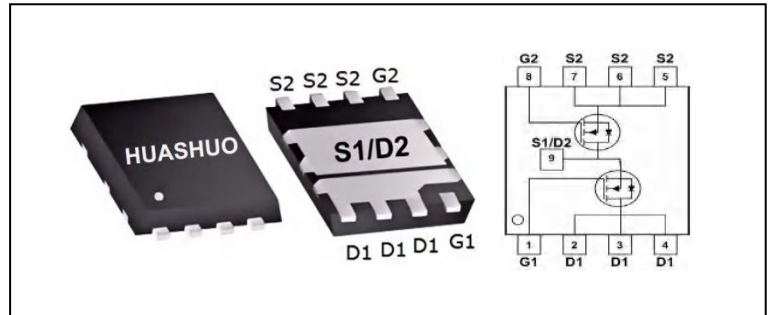
Product Summary

BVDSS	$R_{DS(ON)}$, typ	ID
30V	4.0 m Ω	58A
30V	1.6 m Ω	99A

Applications

- Power Management in Desktop Computer
- DC/DC Converters.
- Isolated DC/DC Converters in Telecom and Industrial.

PRPAK5*6 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating		Units
		Die1	Die2	
V_{DS}	Drain-Source Voltage	30	30	V
V_{GS}	Gate-Source Voltage	± 20	± 20	V
$I_D@T_C=25^{\circ}C$	Continuous Drain Current, $V_{GS} @ 10V^{1,6}$	58	99	A
$I_D@T_C=100^{\circ}C$	Continuous Drain Current, $V_{GS} @ 10V^{1,6}$	36	63	A
$I_D@T_A=25^{\circ}C$	Continuous Drain Current, $V_{GS} @ 10V^1$	22	35	A
$I_D@T_A=70^{\circ}C$	Continuous Drain Current, $V_{GS} @ 10V^1$	17	28	A
I_{DM}	Pulsed Drain Current ²	120	200	A
EAS	Single Pulse Avalanche Energy ³	11.2	80	mJ
I_{AS}	Avalanche Current	15	40	A
$P_D@T_C=25^{\circ}C$	Total Power Dissipation ⁴	25	35	W
$P_D@T_A=25^{\circ}C$	Total Power Dissipation ⁴	3.6	6.3	W
T_{STG}	Storage Temperature Range	-55 to 150	-55 to 150	$^{\circ}C$
T_J	Operating Junction Temperature Range	-55 to 150	-55 to 150	$^{\circ}C$

Thermal Data

Symbol	Parameter	Typ. D1	Typ. D2	Max. D1	Max. D2	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	---	62	62	$^{\circ}C/W$
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹ ($t \leq 10S$)	---	---	35	29	$^{\circ}C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	---	5	3.6	$^{\circ}C/W$



30V DUAL Asymmetric N-CH MOSFETs

Die1 N-Channel Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	30	---	---	V
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V, I _D =15A	---	4.0	5.0	mΩ
		V _{GS} =4.5V, I _D =15A	---	6.6	7.5	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	1.4	1.7	2.2	V
I _{DSS}	Drain-Source Leakage Current	V _{DS} =24V, V _{GS} =0V, T _J =25°C	---	---	1	uA
		V _{DS} =24V, V _{GS} =0V, T _J =55°C	---	---	5	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
R _g	Gate Resistance	V _{DS} =0V, V _{GS} =0V, f=1MHz	---	1.9	---	Ω
Q _g	Total Gate Charge	V _{DS} =15V, V _{GS} =4.5V, I _D =15A	---	8.5	---	nC
Q _{gs}	Gate-Source Charge		---	2.9	---	
Q _{gd}	Gate-Drain Charge		---	3.5	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =15V, V _{GS} =10V, R _G =3.3Ω I _D =15A	---	7	---	ns
T _r	Rise Time		---	42	---	
T _{d(off)}	Turn-Off Delay Time		---	16	---	
T _f	Fall Time		---	6.2	---	
C _{iss}	Input Capacitance	V _{DS} =15V, V _{GS} =0V, f=1MHz	---	882	---	pF
C _{oss}	Output Capacitance		---	380	---	
C _{rss}	Reverse Transfer Capacitance		---	65	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current ^{1,5,6}	V _G =V _D =0V, Force Current	---	---	28	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =1A, T _J =25°C	---	---	1.2	V
trr	Reverse Recovery Time	IF=15A, di/dt=100A/μs, T _J =25°C	---	27	---	nS
Qrr	Reverse Recovery Charge		---	14	---	nC

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 20Z copper.
- 2.The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3.The EAS data shows Max. rating . The test condition is V_{DD}=25V,V_{GS}=10V,L=0.1mH,I_{AS}=35A
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.
- 6.Package limitation current is 28A.



Die2 N-Channel Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	30	---	---	V
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V, I _D =20A	---	1.6	2.2	mΩ
		V _{GS} =4.5V, I _D =20A	---	2.3	3.5	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	1.4	1.7	2.2	V
I _{DSS}	Drain-Source Leakage Current	V _{DS} =24V, V _{GS} =0V, T _J =25°C	---	---	1	uA
		V _{DS} =24V, V _{GS} =0V, T _J =55°C	---	---	5	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
R _g	Gate Resistance	V _{DS} =0V, V _{GS} =0V, f=1MHz	---	2.1	---	Ω
Q _g	Total Gate Charge (4.5V)	V _{DS} =15V, V _{GS} =4.5V, I _D =20A	---	26.1	---	nC
Q _{gs}	Gate-Source Charge		---	8	---	
Q _{gd}	Gate-Drain Charge		---	10.6	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =15V, V _{GS} =10V, R _G =3.3Ω I _D =20A	---	11.5	---	ns
T _r	Rise Time		---	45.5	---	
T _{d(off)}	Turn-Off Delay Time		---	28.5	---	
T _f	Fall Time		---	7.1	---	
C _{iss}	Input Capacitance	V _{DS} =15V, V _{GS} =0V, f=1MHz	---	2859	---	pF
C _{oss}	Output Capacitance		---	1259	---	
C _{rss}	Reverse Transfer Capacitance		---	229	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current ^{1,5,6}	V _G =V _D =0V, Force Current	---	---	37	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =1A, T _J =25°C	---	---	1.2	V
t _{rr}	Reverse Recovery Time	I _F =20A, di/dt=100A/μs, T _J =25°C	---	50	---	nS
Q _{rr}	Reverse Recovery Charge		---	52	---	nC

Note :

1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.

2.The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%

3.The EAS data shows Max. rating. The test condition is V_{DD}=25V, V_{GS}=-10V, L=0.1mH, I_{AS}=-40A

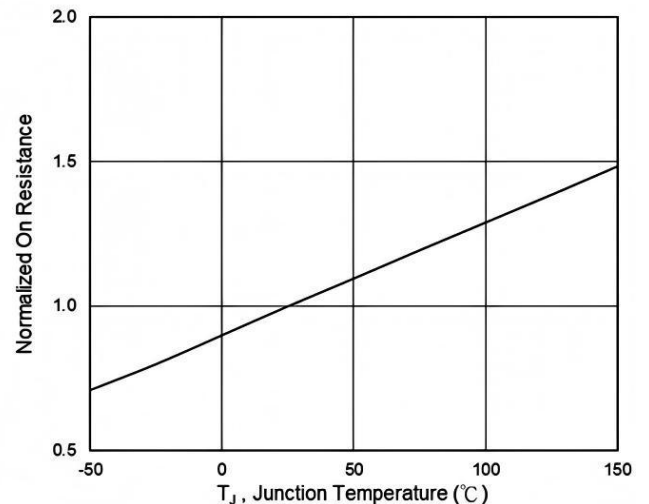
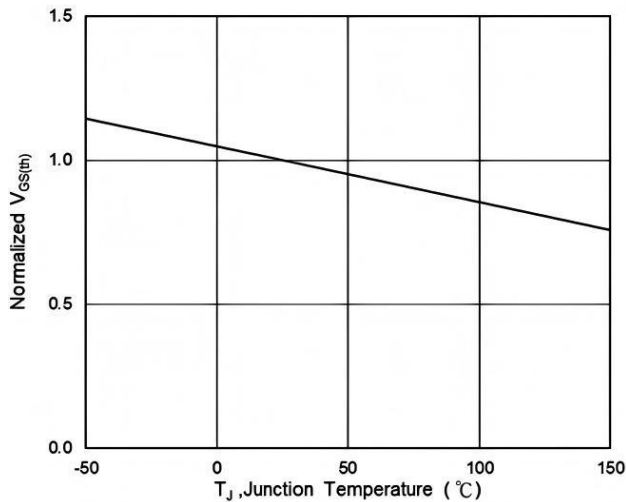
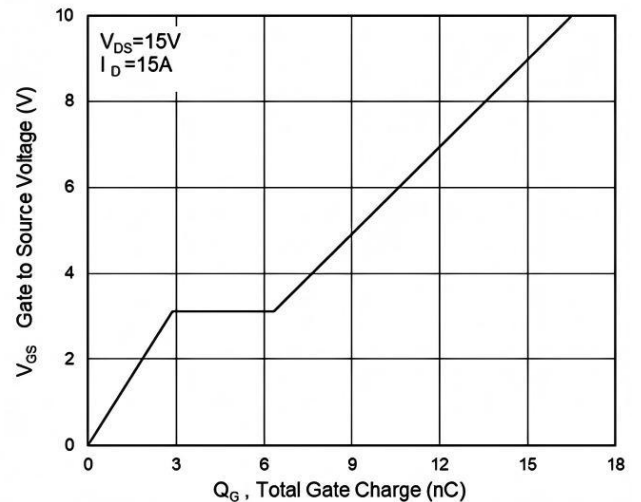
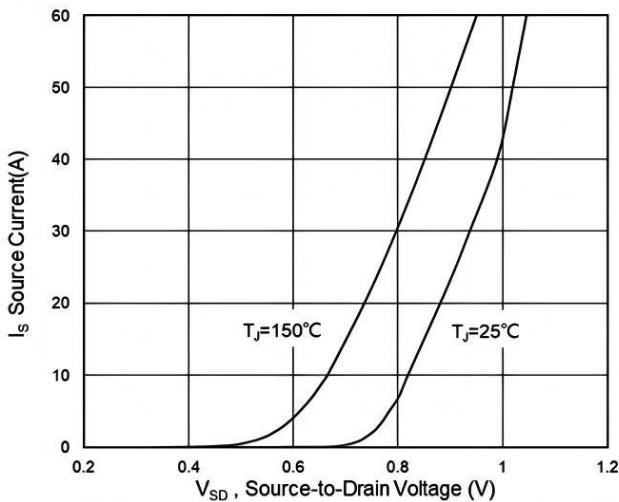
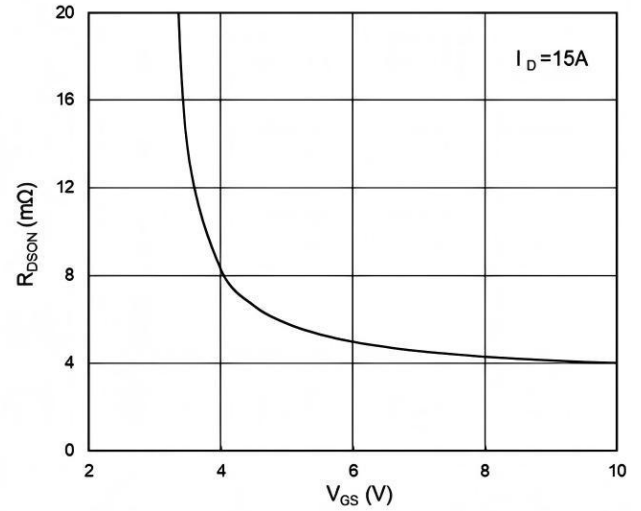
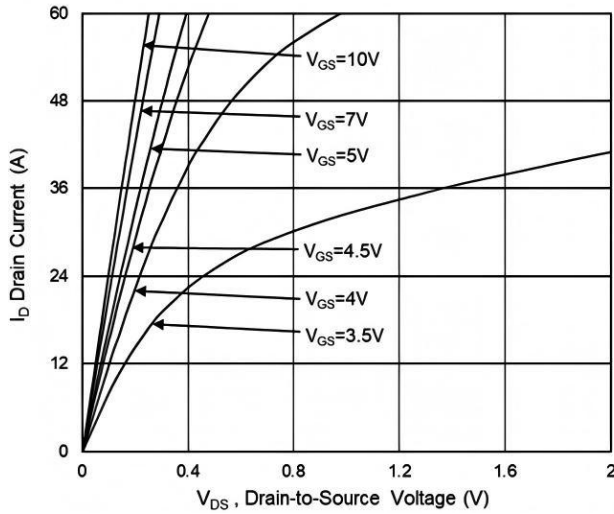
4.The power dissipation is limited by 150°C junction temperature

5.The data is theoretically the same as I_D and I_{DM}, in real applications, should be limited by total power dissipation.

6.Package limitation current is 37A.



N-Channel Typical Characteristics(Die1)





30V DUAL Asymmetric N-CH MOSFETs

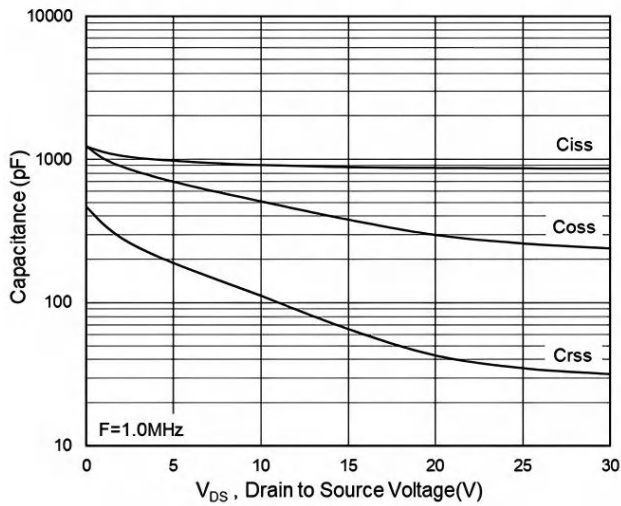


Fig.7 Capacitance

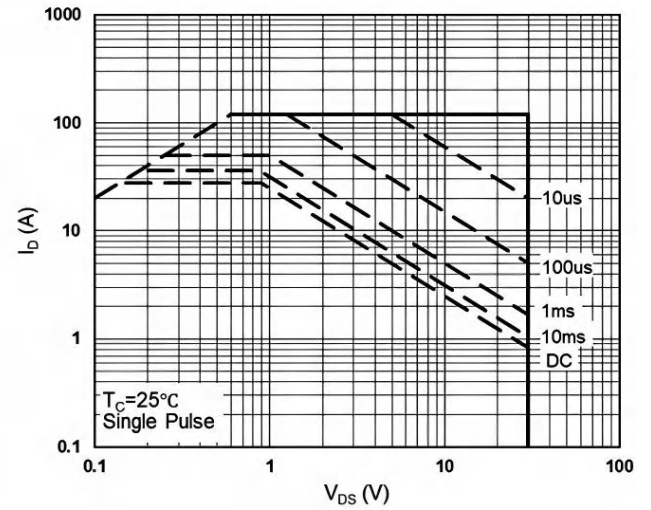


Fig.8 Safe Operating Area

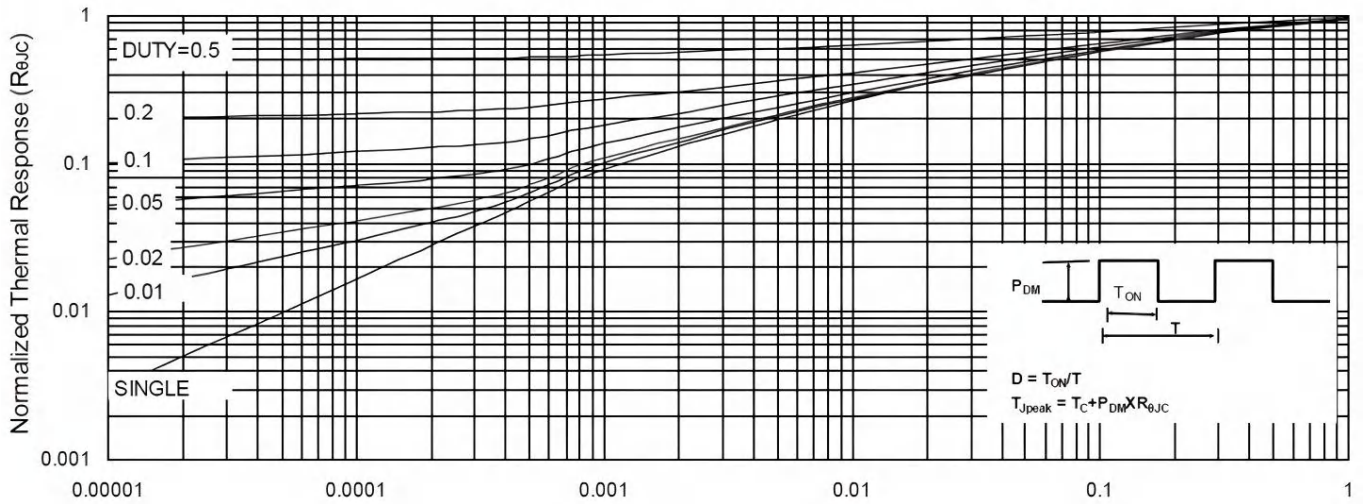


Fig.9 Normalized Maximum Transient Thermal Impedance

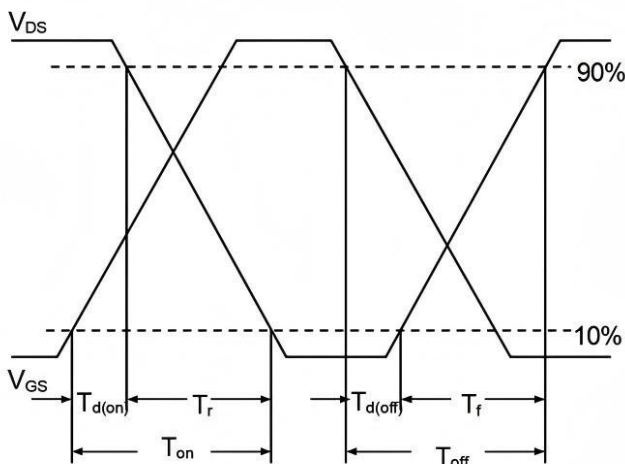


Fig.10 Switching Time Waveform

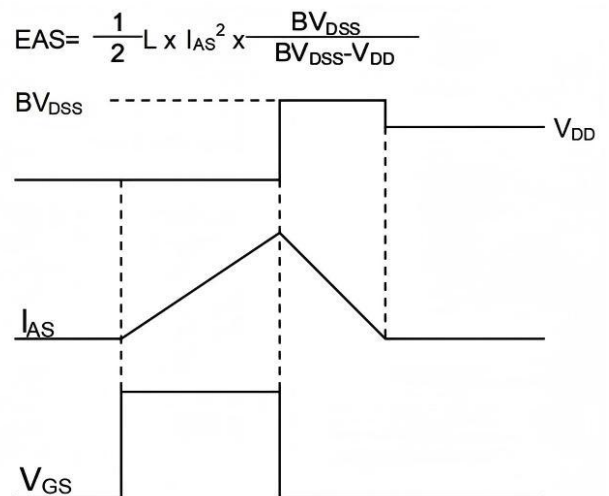
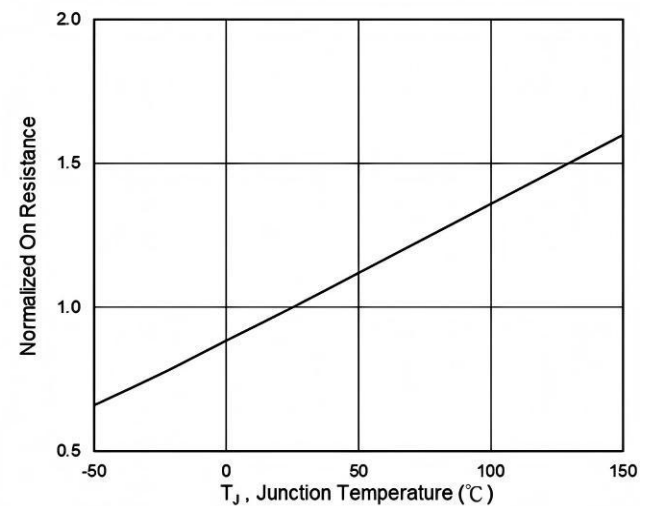
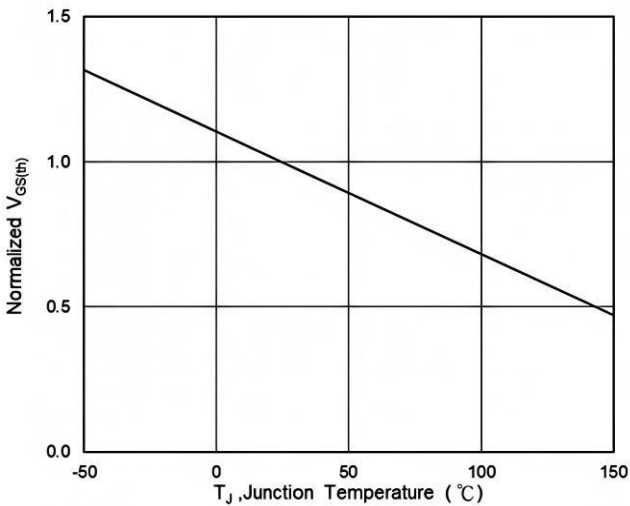
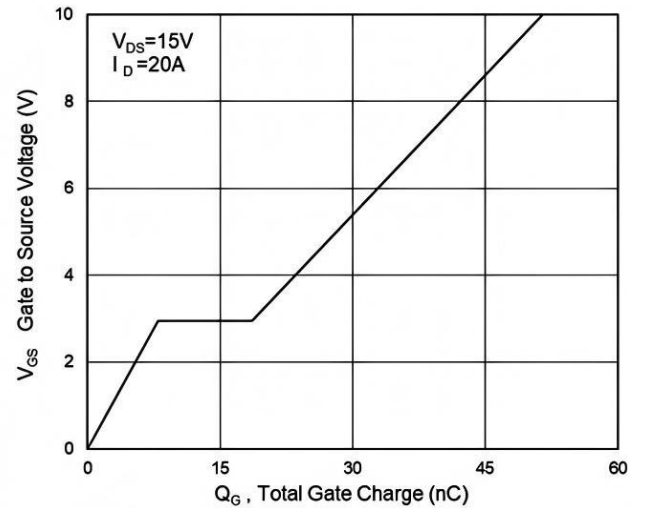
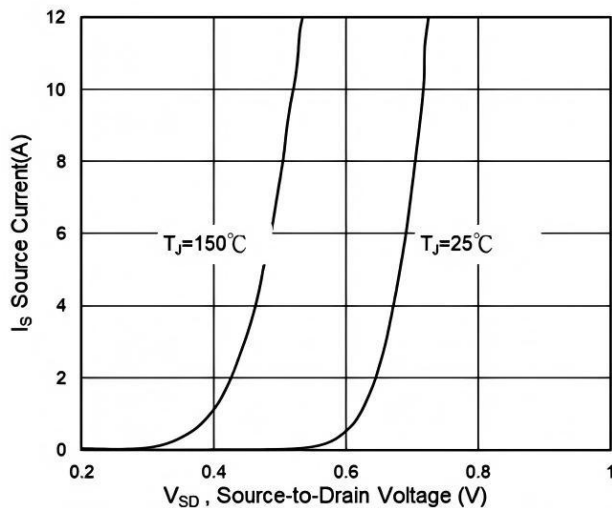
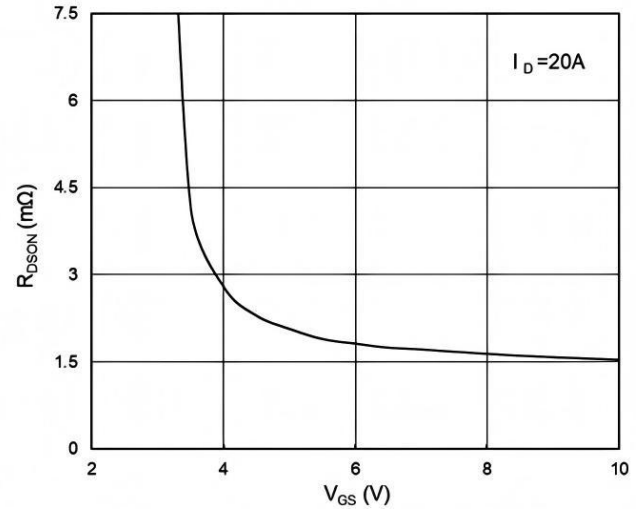
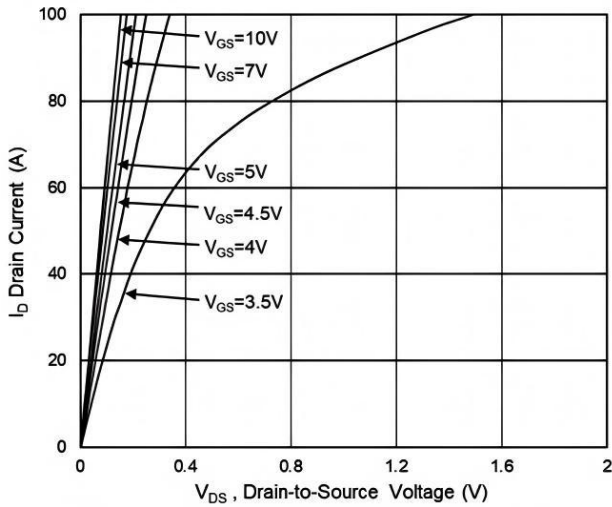


Fig.11 Unclamped Inductive Switching Wave



N-Channel Typical Characteristics(Die2)





30V DUAL Asymmetric N-CH MOSFETs

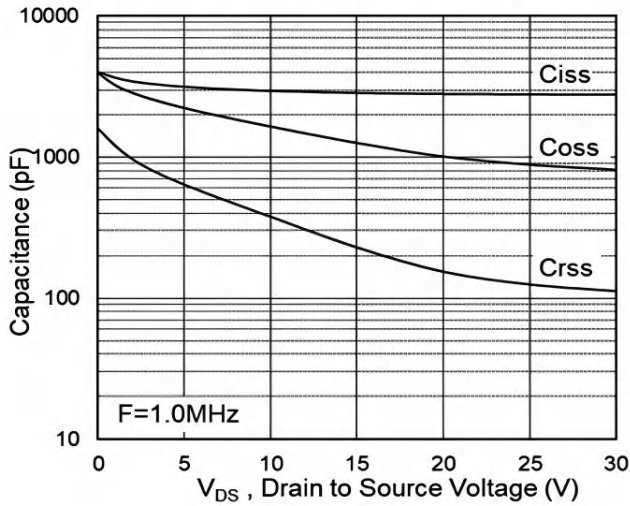


Fig.7 Capacitance

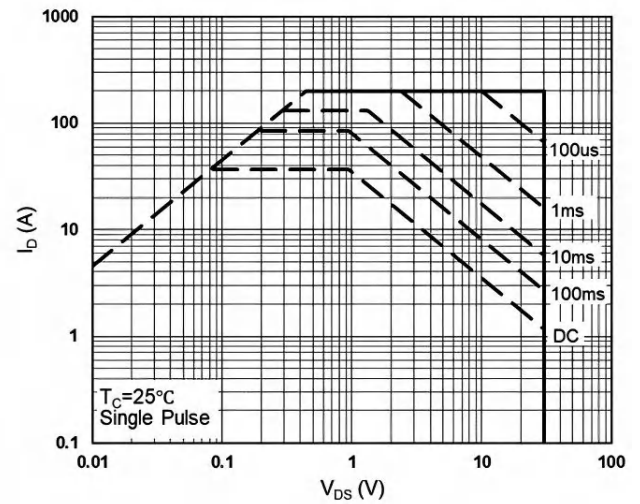


Fig.8 Safe Operating Area

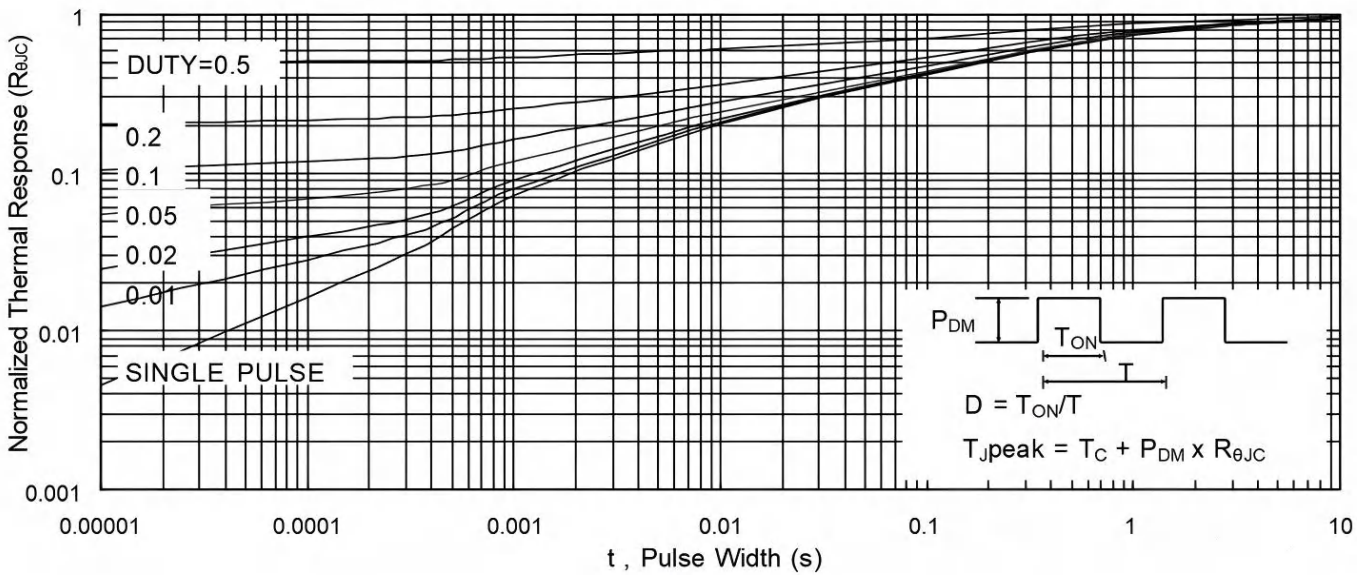


Fig.9 Normalized Maximum Transient Thermal Impedance

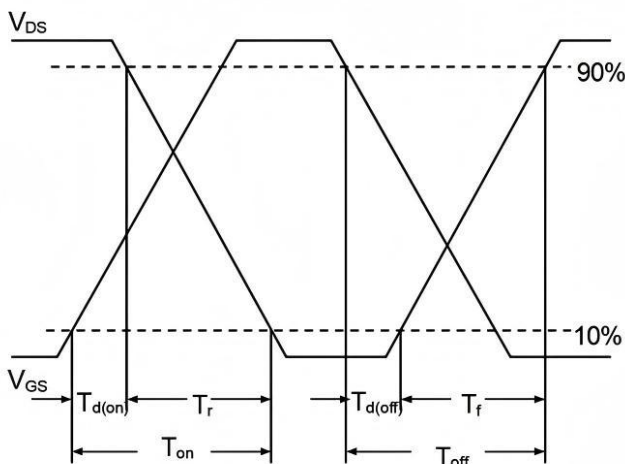


Fig.10 Switching Time Waveform

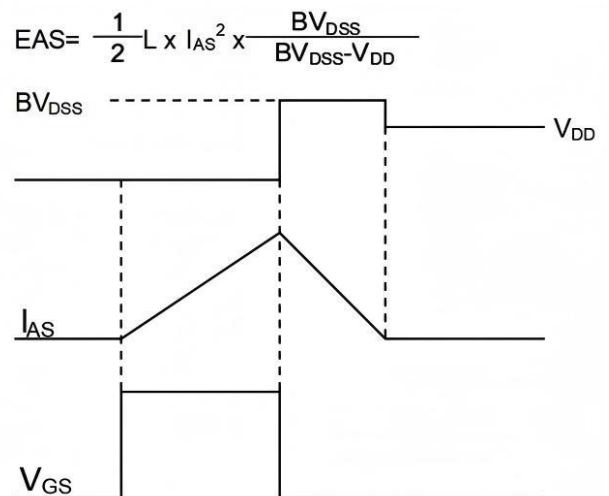


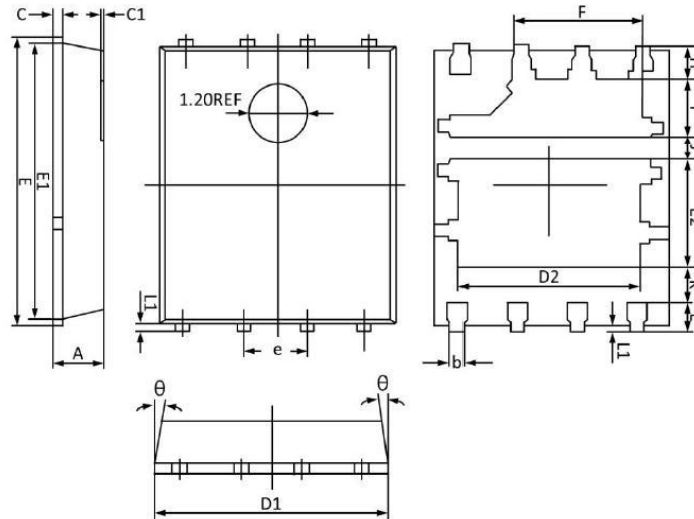
Fig.11 Unclamped Inductive Switching Wave



Ordering Information

Part Number	Package code	Packaging
HSBA3482	PRPAK5*6	3000/Tape&Reel

PRPAK5*6 Dual Package Outline



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.100	0.036	0.043
b	0.330	0.510	0.013	0.020
C	0.200	0.300	0.008	0.011
C1	0.040 REF		0.040 REF	
D1	4.800	5.000	0.189	0.196
D2	3.610	3.960	0.143	0.155
E	5.900	6.100	0.233	0.240
E1	5.700	5.800	0.225	0.228
E2	2.020	2.420	0.080	0.095
e	1.270BSC		1.270BSC	
F	2.550	2.900	0.101	0.114
H	0.610	0.810	0.025	0.031
I	1.100	1.300	0.044	0.051
J	0.400	0.600	0.016	0.023
K	0.500	-	0.020	-
L	0.510	0.710	0.020	0.027
L1	0.060	0.200	0.003	0.007
θ	0°	12°	0°	12°

HSBA3482 Marking:

